

IN THE ABSTRACT

Please amend the Abstract as shown below:

A method for forming contact openings in various locations of the upper surface of an integrated circuit ~~comprising~~ having raised areas, critical openings having to be formed between two neighboring raised areas, ~~comprising~~ including the steps of covering the entire structure with a first protection layer; forming non-critical openings in the first protection layer; coating the structure with a second protection layer; performing an oblique irradiation so that the second protection layer is not irradiated at the bottom of the regions located between two raised areas; removing the non-irradiated portions of the second protection layer; removing the portions of the first protection layer located under the second protection layer at the locations where this second protection layer has been removed; and removing the irradiated portions of the second protection layer.